	L #	Search Text	DBs
1	L1	("6335211").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
2	L10	etch$3 with pattern	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
3	L11	insulat$3 near3 (substrate wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
4	L12	thin near4 film near4 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
5	L13	"TFT"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
6	L14	12 13	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
7	L15	2 with 3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
8	L16	5 with 6 with (gate near3 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
9	L17	7 with 6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
10	L18	8 with 9	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
11	L19	15 and 16 and 17 and 18	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB

	L #	Search Text	DBs
12	L2	gate near3 wire	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
13	L20	19 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
14	L21	20 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
15	L22	15 same 16 same 17 same 18	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
16	L23	22 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
17	L24	22 same 10	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
18	L25	24 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
19	L26	25 and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
20	L27	22 same 14	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
21	L28	27 same 11	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
22	L29	11 with (known conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB

	L #	Search Text	DBs
23	L3	(gate near3 line) with (gate near3 electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
24	L30	27 same 29	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
25	L31	27 and 29	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
26	L32	22 same 29	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
27	L33	14 same 29	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
28	L34	22 and 29	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
29	L35	(257/293).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
30	L36	(257/444).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
31	L37	(257/E27.141).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
32	L38	(349/43).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
33	L4	gate near4 ((insulating near3 layer) oxide nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB

	L #	Search Text	DBs
34	L5	data near3 wire	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
35	L6	data near3 line	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
36	L7	source near4 electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
37	L8	drain near4 electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
38	L9	pixel near4 electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB